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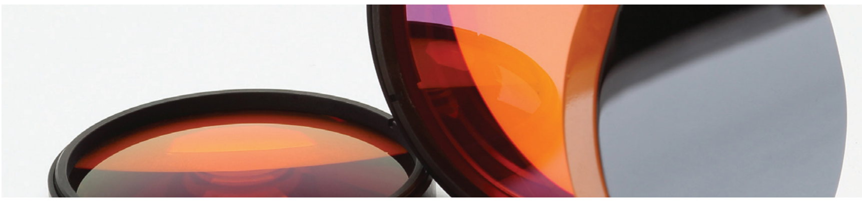

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INFORMATION FOR AUTHORS AND READERS

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2. The manuscripts both in Polish and in English can be submitted. Due to introducing all the articles printed in *Electronic Materials* to the Internet , the author should make a statement on the copyright transfer of the author's economic rights to the Publisher.

3. Concerned about the reliability of the scientific work and the development of an ethical attitude of a researcher, a procedure has been introduced in order to prevent any cases of scientific dishonesty and unethical attitudes, defined as *ghostwriting* and *guest authorship* (*honorary authorship*):

- *ghostwriting* occurs when someone has made a substantial contribution to the publication without revealing his participation as one of the authors or without mentioning his role in the acknowledgments in the publication;
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The Editors require that the authors disclose the contributions of the individual authors in the preparation of a multi-author work, giving their affiliations and the information on their participation in the creative process, i.e. the information on the authors of the work's idea, assumptions, methods, etc. that have been utilized during the article preparation. The main responsibility for this information is borne by the author submitting the manuscript.

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II. Procedure of articles review and approval for print

1. The author's materials directed for print in "Electronic Materials" are subjected to evaluation by the independent reviewers and the members of the Editorial Board.

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3. At least two independent reviewers from outside the research institution affiliated by the author of the publication are called for the evaluation of each publication.

4. In case of a publication in a foreign language, at least one reviewer is called, affiliated in a foreign institution with the seat in a country other than that of the origin of the author of the manuscript.

5. The author or authors of the manuscript and the reviewers do not know their identities (the so-called "double-blind review process").

6. A review is in written form and contains a clear conclusion of the reviewer concerning the article acceptance for the publication (without corrections or with necessary amendments to be made by the author) or its rejection.

7. The criteria for the article acceptance or rejection and a possible review form are disclosed to the public on the website of *Electronic Materials.*

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10. The Editor-in-chief refuses to publish the authors' materials in the following cases:

- the contents of the manuscript are illicit,
- any signs of the scientific dishonesty, and especially *ghostwriting* and *guest authorship*, will be found out,
- the work has not received a positive final evaluation from the reviewers and the thematic editor.

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- the topic of the work is not in line with the subject field of *Electronic Materials*,
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- the author refuses to make any necessary amendments proposed by the reviewer and the Editorial Board,
- the text or the illustrations provided by the author do not meet the technical requirements.

LIST OF REVIEWERS 2020

INSTRUCTIONS FOR AUTHORS

The editorial office of *Electronic Materials* kindly asks the authors for sending the ordered articles by e-mail to the address ointe@itme.edu.pl or on a magnetic medium, according to the following specifications:

TEXT

a) The article content should be delivered in the files with an extension supported by Word software (DOC and DOCX as the best file formats). The text should be written in a continuous manner, divided into consecutively numbered sections with the titles. The symbols of the variables should be written in italics. The approximate locations of the illustrations should be indicated in the text of the manuscript; however, any illustrations should not be imported into the text file but placed as the separate files (see point 4).

b) The captions to the illustrations, both in Polish and in English, should also be provided as the separate files.

c) The following items should be present on first page of the article: the given name and family name of the author, degree, authors affiliation, postal address, e-mail, the article title, both in Polish and in English.

ABSTRACT

a) The abstracts, in Polish and in English, should be attached to the article. Each abstract version should not exceed 200 words.

b) Keywords, both in both Polish and in English, should also be added.

REFERENCES

a) The references should be cited in the text in square brackets in order of their appearance in the text.

b) Reference style:

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- **Multi-author edited work:**
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  Author: Book title. Edition. Publication place: Publisher's name, Publication year, ISBN. Section (chapter) title, section (chapter) pages.
- **Book section (chapter) from a multi-author work:**
  Author: Section (chapter) title. Book title. Publication place: Publisher's name, Publication year, ISBN.
- **Journal article:**
  Author: Article Title. „Journal title" Year, Volume, Number, Pages.
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  Author: Article title [online], Year, Volume, Number [Access - date] Pages, URL. ISSN.
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a) Each illustrative material should be saved in a separate file (PCX, TIFF, BMP, WFM, CES, JPG) with a resolution not less than 150 dpi.

b) In case of the illustrative materials that have not been originally created by the author(s), the original source should be cited in the references.

FORMULAS

a) The formulas should be numbered consecutively with Arabic numerals

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THE AUTHOR ARE OBLIGED TO PROOFREADING

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The *Institute of Electronic Materials Technology* develops advanced innovative production technologies of materials characterized by a perfect crystallographic structure and excellent properties, as well as components based on these materials. The scope of R&D activities carried out covers the following areas:

Materials for next-generation components:

- graphene;
- topological insulators;
- materials for spintronics;
- self-organising materials;
- photonic crystals, including plasmonic materials and metamaterials.

Materials for energy generation, storage and transfer:

- wide gap semiconductors, including silicon carbide for GaN HEMT transistors;
- semiconductor-doped glass optical fibres for photovoltaics;
- eutectic materials for photovoltaics;
- SiC wafers and SiC epitaxial layers;
- glass-ceramic seals for fuel cells;
- thermoelectric materials;
- inert matrices for a safe storage of radioactive waste;
- electrode materials for lithium ion batteries;
- ceramic-metal composites and FGMs.

Materials for photonics:

- materials for III-V based semiconductor lasers (obtained using GaAsP, InGaP, AlGaAs, GaAs, GaSb and InP), wafers, epitaxial structures;
- GaN-based epitaxial structures;
- materials for solid state lasers, produced using strontium-calcium niobate;
- infrared photodetectors and UV photodetectors;
- oxide crystals for lasers, passive Q modulators, scintillators, electro-optical and piezoelectric devices, substrates for superconducting HTSc layers;
- glass and ceramics with carefully designed spectral characteristics, including transparent ceramics;
- diffractive optical elements and microlenses;
- nanostructured thin layers;
- luminescent nanopowders and nanocrystals;
- optical fibres and waveguides, including active and photonic fibres.

Materials for electronics:

- silicon monocrystals (standard Si wafers and Si wafers with special properties);
- porous silicon;
- silicon foils;
- epitaxial layers on silicon;
- SiC wafers and SiC epitaxial layers;
- nanopowders and polymer-based powders, pastes and inks for printed electronics;
- photosensitive pastes;
- piezoelectric crystals;
- ceramic-metal composites;
- super-pure metals.

Components:

ITME has elaborated a great number of innovative electronic components based on the manufactured materials, for instance:

- optical fibres (active and photonic), filters, diffractive lenses, two-dimensional photonic microstructures;
- passive elements on membranes (sensors);
- filters, resonators, sensors and actuators based on surface acoustic waves;
- semiconductor devices (lasers, transistors, photodetectors, Schottky diodes);
- solid state lasers and microlasers.

The manufacture of state of the art components is possible at ITME due to high-tech equipment enabling:

- design and manufacture of masks;
- deposition of dielectric thin films ($Si0_2$, Si_3N_4 , AIN);
- multilayer metallization;
- use of lithography: contact printing using deep UV, electron beam pattern generation;
- application of various etching techniques, including reactive ion etching and controlled sidewall etching.

Advanced methods of material properties investigation:

The characterization of materials is performed at ITME by the following methods:

- standard chemical analysis and spectral instrumental methods (flame atomie emission spectrometry, atomie absorption spectroscopy, ultraviolet to far-infrared spectroscopy);
- Mössbauer spectroscopy (conventional, conversion electron method, X radiation method and unique "Mössbauer" method developed at ITME);
- X-ray powder diffraction using the Rietveld method, High Resolution X-ray diffraction, X-ray reflectometry and X-ray diffraction topography;
- scanning electron microscopy and a method based on synchrotron radiation;
- electron paramagnetic resonance;
- atomie force microscopy;
- standard thermal methods (high-temperature microscopy, thermogravimetry, differentia!thermal analysis, dilatometry, etc.) and X-ray methods;
- mechanical methods (testing resistance, friction, hardness, etc.);
- optical methods (microscopy, absorption, reflectometry).

Methods of electronic and photonic components investigation:

ITME tests optoelectronic, microelectronic and piezoelectric devices, using special techniques enabling the characterization of components, including:

- I-V and C-V measurements;
- deep level transient spectroscopy;
- impedance measurements and the measurements of scattering matrix elements up to the frequency of 20 Ghz;
- noise measurements;
- analysis of operational parametres of lasers and photodetectors.